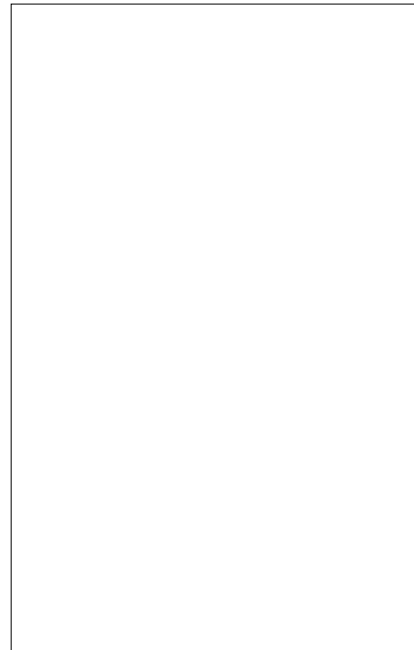


DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT1225C SCR provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. Package TO-220C is RoHS compliant.



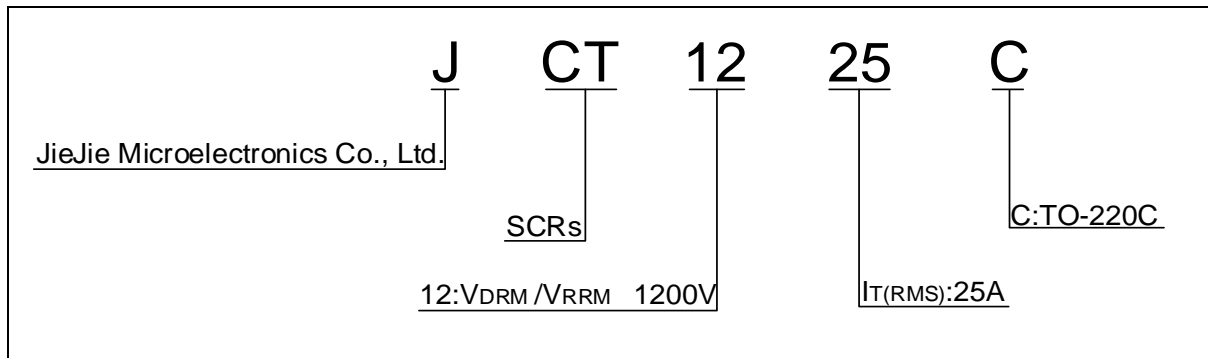
MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	25	A
V_{DRM}/V_{RRM}	1200	V
I_{GT}	"40	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ C$)	V_{DRM}	1200	V
Repetitive peak reverse voltage ($T_j=25^\circ C$)	V_{RRM}	1200	V
Average on-state current ($T_c=96^\circ C$)	$I_{T(AV)}$	16	A
RMS on-state current ($T_c=96^\circ C$)	$I_{T(RMS)}$	25	A
Non repetitive surge peak on-state current ($t_p=10ms, T_j=25^\circ C$)	I_{TSM}	320	A
Non repetitive surge peak on-state current ($t_p=8.3ms, T_j=25^\circ C$)		352	
I^2t value for fusing ($t_p=10ms, T_j=25^\circ C$)	I^2t	512	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}, f=100Hz, T_j=125^\circ C$)	di/dt	200	A/s
Peak gate current ($t_p=20\mu s, T_j=125^\circ C$)	I_{GM}	5	A
Average gate power dissipation ($T_j=125^\circ C$)	$P_{G(AV)}$	1	W

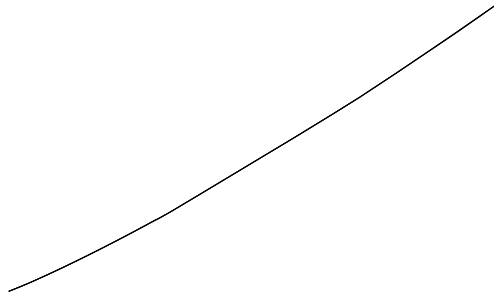
ORDERING INFORMATION



MARKING

FIG.1: Maximum power dissipation versus RMS on-state current

FIG.2: RMS on-state current versus case temperature



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